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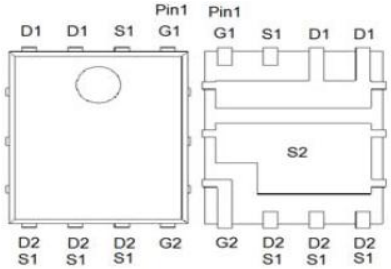
RoHS Compliant

PK610DZ

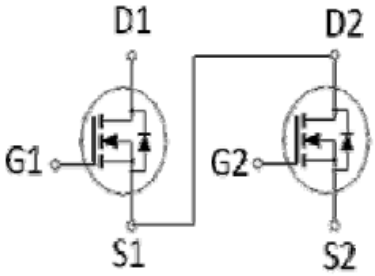
Dual N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D	CH.
30V	1.2mΩ @V_{GS} = 10V	127A	Q2
30V	6.5mΩ @V_{GS} = 10V	43A	Q1



PDFN 5*6P



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	CH.	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	Q2	30	V
			Q1	30	
Gate-Source Voltage		V_{GS}	Q2	±20	
			Q1	±20	
Continuous Drain Current[3]	T_C = 25 °C	I_D	Q2	127	A
			Q1	43	
	T_C = 100 °C		Q2	80	
			Q1	27	
Pulsed Drain Current[1]		I_{DM}	Q2	160	
			Q1	100	
Continuous Drain Current	T_A = 25 °C	I_D	Q2	32	
			Q1	11	
	T_A = 70 °C		Q2	25	
			Q1	9.4	
Avalanche Current		I_{AS}	Q2	68.6	
			Q1	25	
Avalanche Energy	L = 0.1mH	E_{AS}	Q2	235	mJ
			Q1	31	
Power Dissipation	T_C = 25 °C	P_D	Q2	39	W
			Q1	24	
	T_C = 100 °C		Q2	15	
			Q1	9.8	

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Dual N-Channel Enhancement Mode MOSFET

Power Dissipation	T_A = 25 °C	P_D	Q2	2.5	W
			Q1	1.7	
	T_A = 70 °C		Q2	1.6	
			Q1	1.1	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	CH.	TYPICA	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$	Q2		50	°C / W
		Q1		70	
Junction-to-Case	$R_{\theta JC}$	Q2		3.2	
		Q1		5.1	

[1]Pulse width limited by maximum junction temperature $T_{J(MAX)}$=150°C.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.The value in any given application depends on the user's specific board design.

[3]Package limitation current :Q1=35A,Q2=35A.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	CH.	LIMITS			UNITS
				MIN	TYP	MAX	
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	Q2	30			V
			Q1	30			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	Q2	1.3	1.8	2.3	
			Q1	1.3	1.6	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	Q2			±100	nA
			Q1			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V	Q2			1	μA
			Q1			1	
		V_{DS} = 20V, V_{GS} = 0V , T_J = 55 °C	Q2			10	
			Q1			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 16A	Q2		1.2	1.6	mΩ
		V_{GS} = 4.5V, I_D = 11A	Q1		6	9.5	
		V_{GS} = 10V, I_D = 20A	Q2		0.85	1.2	
		V_{GS} = 10V, I_D = 11A	Q1		4.3	6.5	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A	Q2		68		S
		V_{DS} = 5V, I_D = 11A	Q1		50		

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Dual N-Channel Enhancement Mode MOSFET

DYNAMIC							
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	Q2		4056		pF
			Q1		888		
Output Capacitance	C_{oss}		Q2		782		
			Q1		171		
Reverse Transfer Capacitance	C_{rss}		Q2		456		
			Q1		99		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz	Q2		1		Ω
			Q1		1.1		
Total Gate Charge[2]	Q_g V_{GS}=10V	Q2 V_{DS} = 15V , V_{GS} = 10V, I_D = 20A Q1 V_{DS} = 15V , V_{GS} = 10V, I_D = 11A	Q2		81		nC
			Q1		17.3		
	Q_g V_{GS}=4.5V		Q2		43		
			Q1		9.3		
Gate-Source Charge[2]	Q_{gs}		Q2		12		
			Q1		2.5		
Gate-Drain Charge[2]	Q_{gd}		Q2		19		
			Q1		4.7		
Turn-On Delay Time[2]	$t_{d(on)}$	Q2 V_{DS} = 15V,I_D ≅ 20A, V_{GS}=10V, R_{GEN}= 6Ω Q1 V_{DS} = 15V ,I_D ≅ 11A, V_{GS} = 10V, R_{GEN} =6Ω	Q2		30		nS
			Q1		21		
Rise Time[2]	t_r		Q2		19		
			Q1		15		
Turn-Off Delay Time[2]	$t_{d(off)}$		Q2		61		
			Q1		46		
Fall Time[2]	t_f		Q2		21		
			Q1		15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)							
Continuous Current[3]	I_S		Q2			39	A
			Q1			20	
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V	Q2			1	V
		I_F = 11A, V_{GS} = 0V	Q1			1.2	
Reverse Recovery Time	t_{rr}	Q2 I_F = 20A, dI_F/dt = 100A /μs Q1 I_F = 11A, dI_F/dt = 100A /μS	Q2		28		nS
			Q1		8.2		
Reverse Recovery Charge	Q_{rr}		Q2		15		nC
			Q1		1.3		

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Package limitation current :Q1=35A,Q2=35A.

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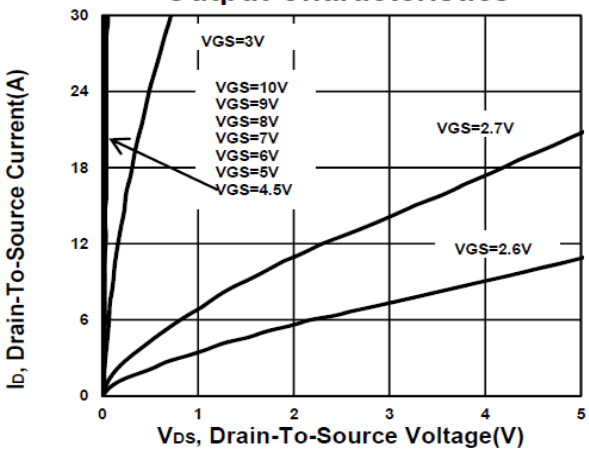
RoHS Compliant

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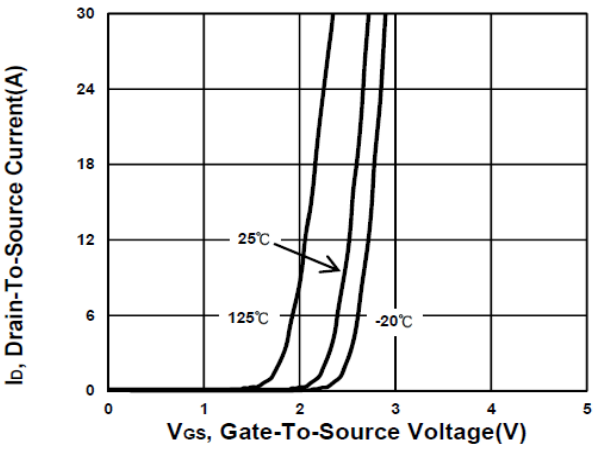
Dual N-Channel Enhancement Mode MOSFET

Q2

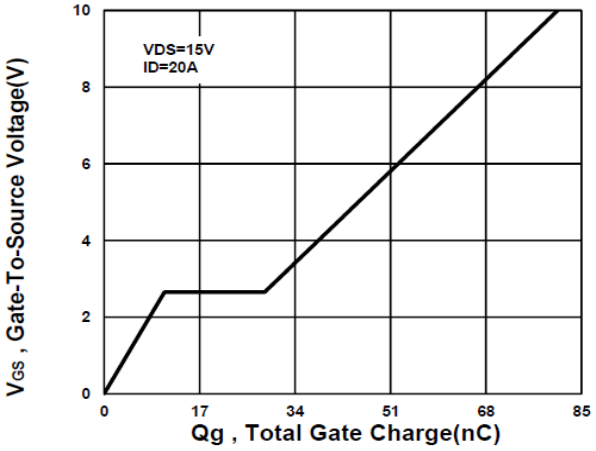
Output Characteristics



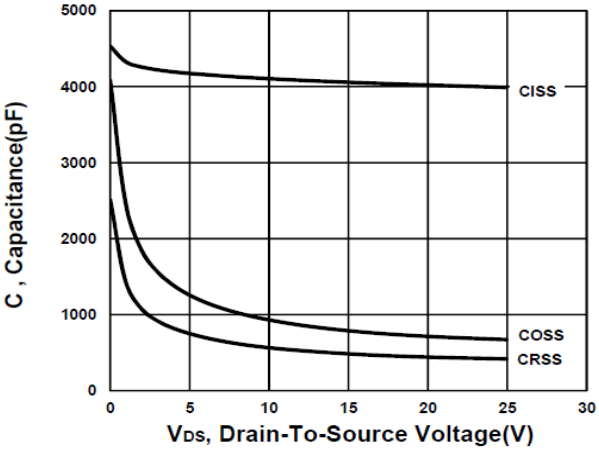
Transfer Characteristics



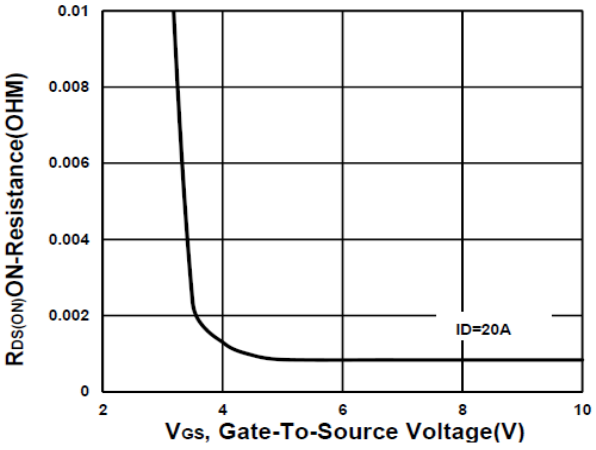
Gate charge Characteristics



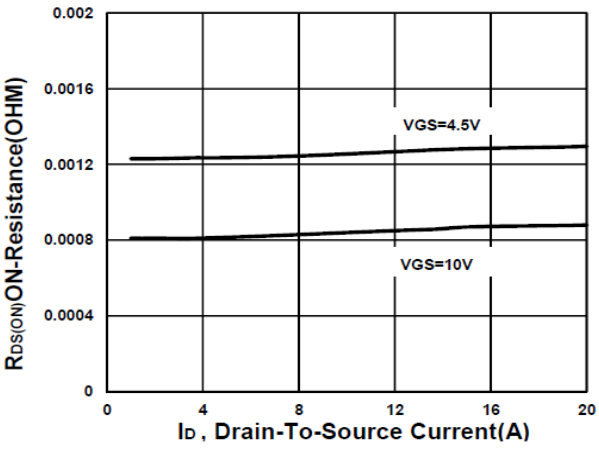
Capacitance Characteristic



On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



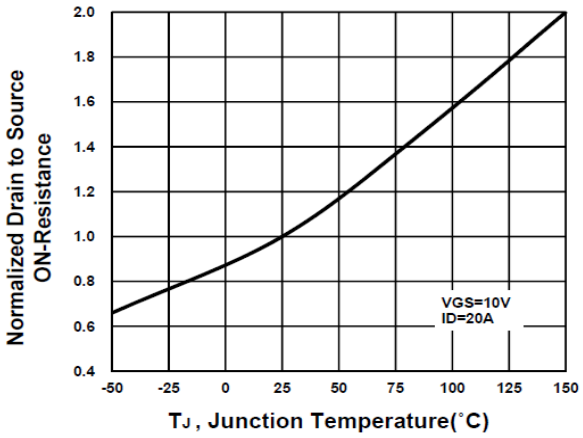
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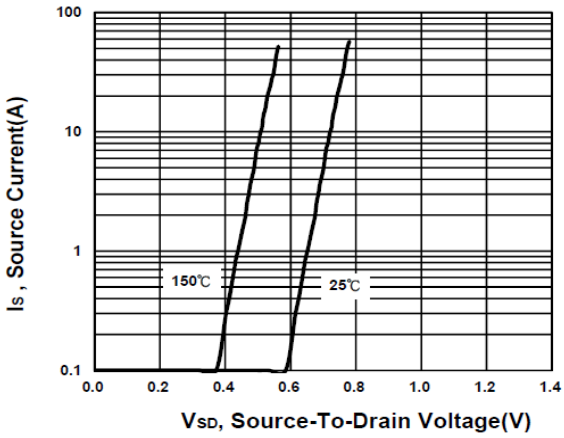
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Dual N-Channel Enhancement Mode MOSFET

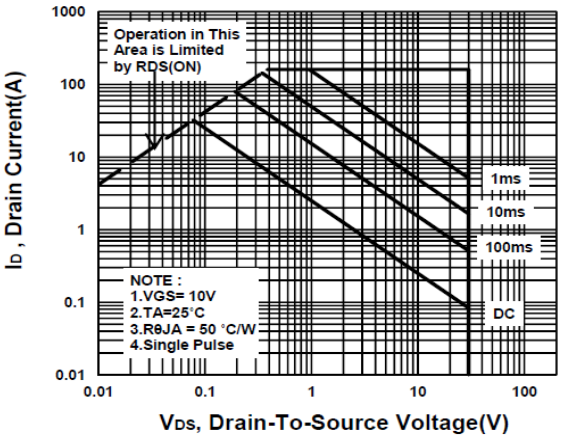
On-Resistance VS Temperature



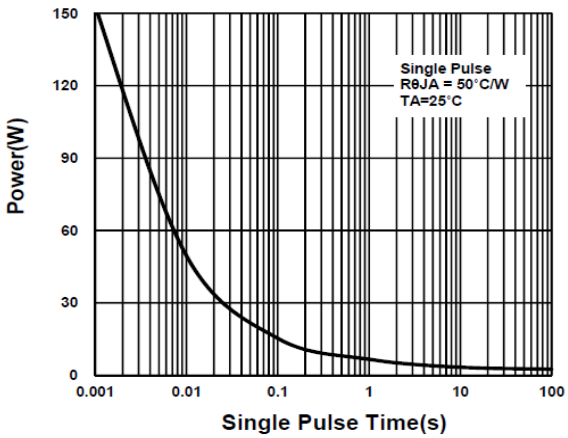
Source-Drain Diode Forward Voltage



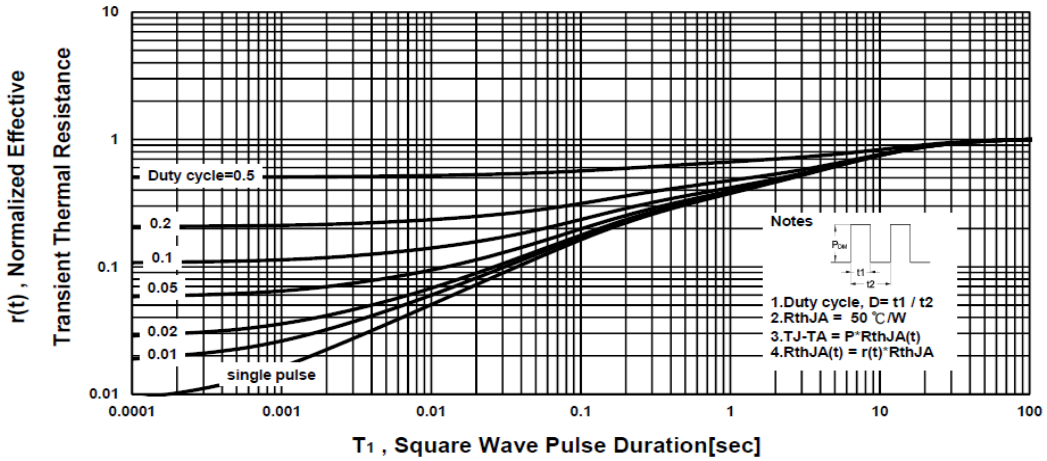
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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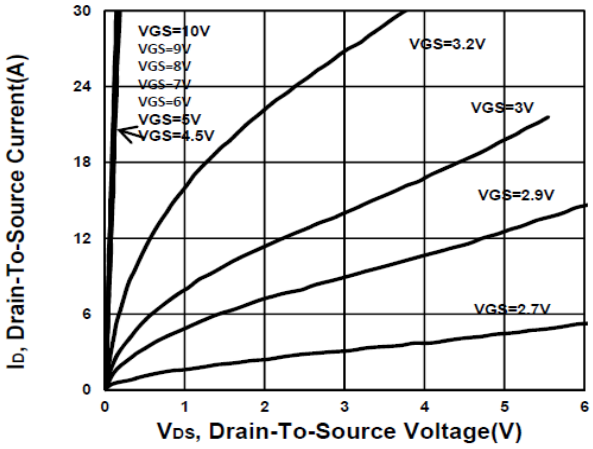
RoHS Compliant

PK610DZ

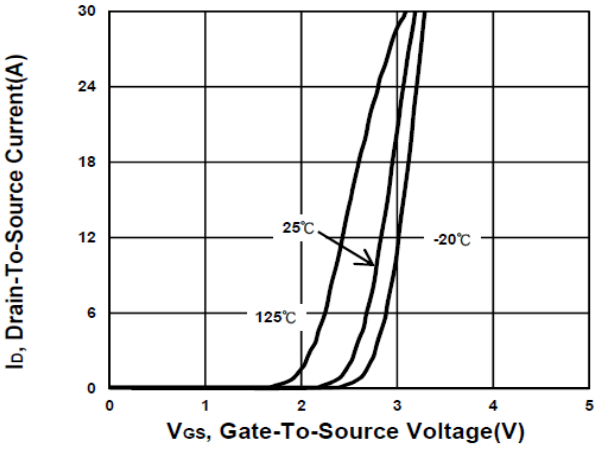
Dual N-Channel Enhancement Mode MOSFET

Q1

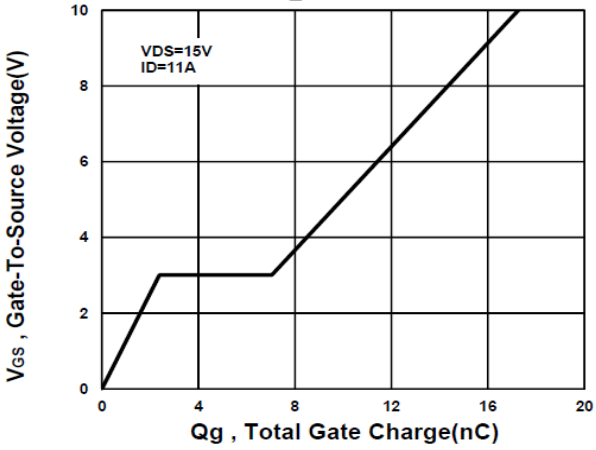
Output Characteristics



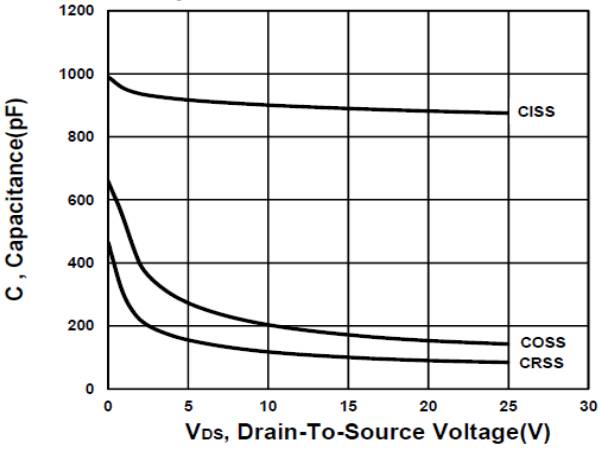
Transfer Characteristics



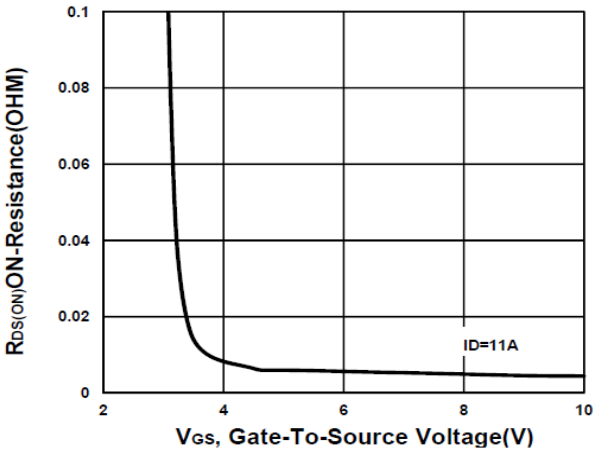
Gate charge Characteristics



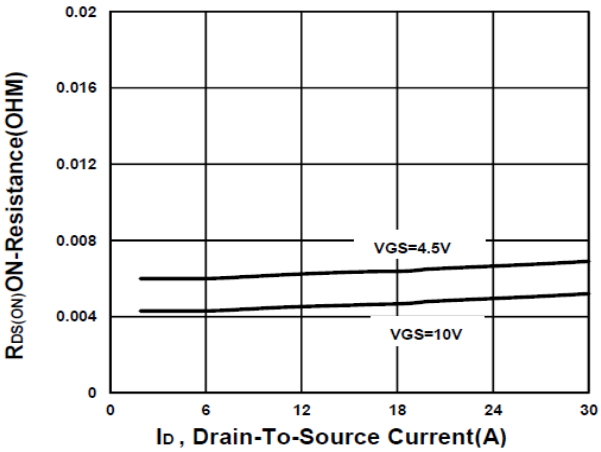
Capacitance Characteristic



On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



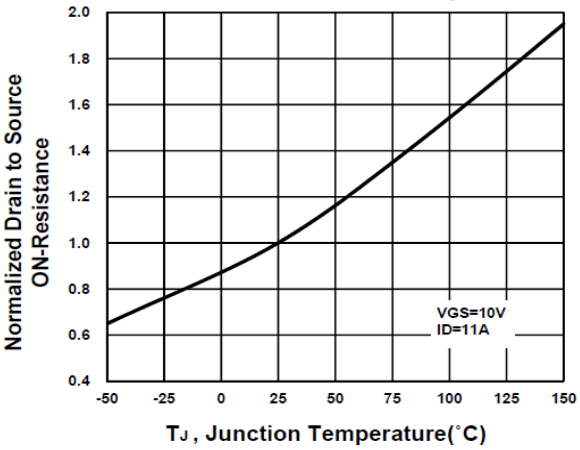
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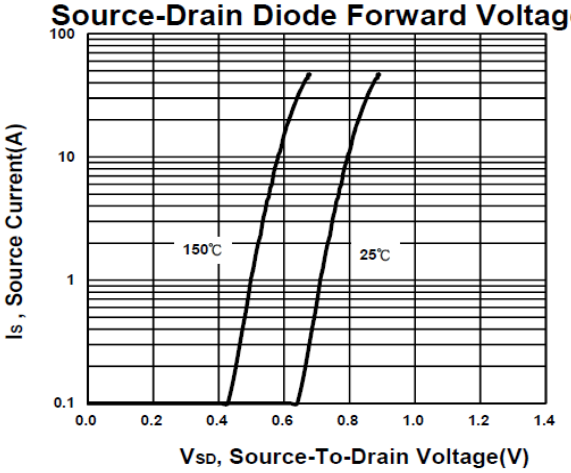
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Dual N-Channel Enhancement Mode MOSFET

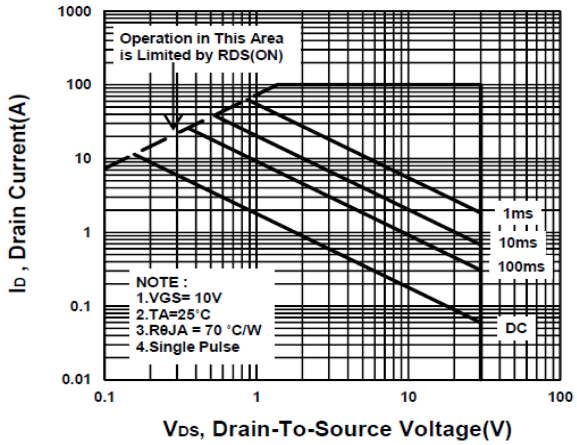
On-Resistance VS Temperature



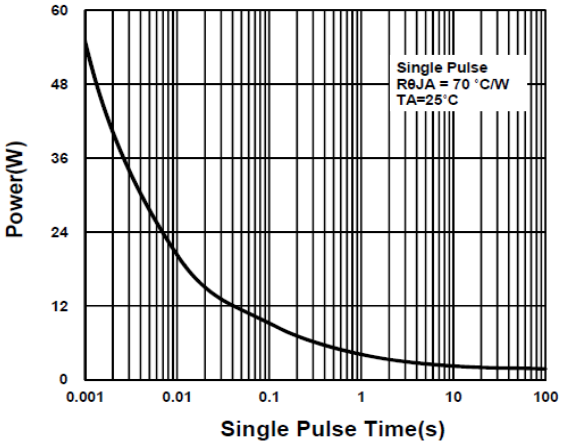
Source-Drain Diode Forward Voltage



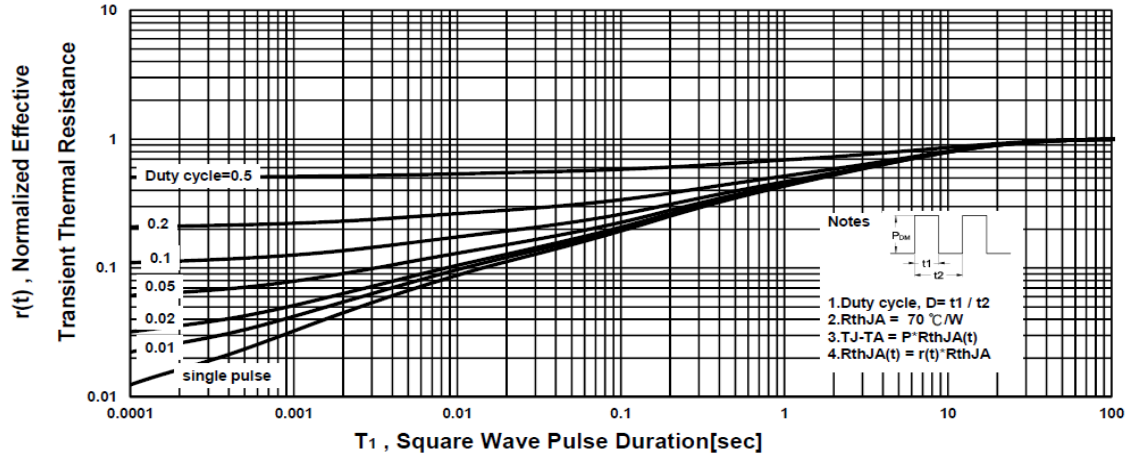
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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RoHS Compliant

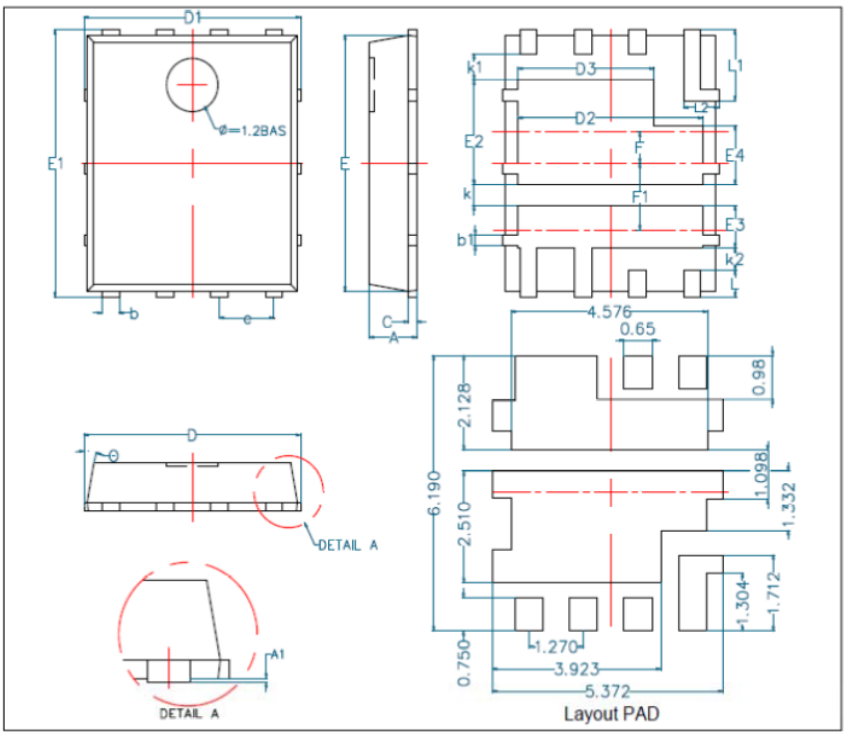
PK610DZ

Dual N-Channel Enhancement Mode MOSFET

Package Dimension

PDFN 5x6P(Dual flip chip) MECHANICAL DATA

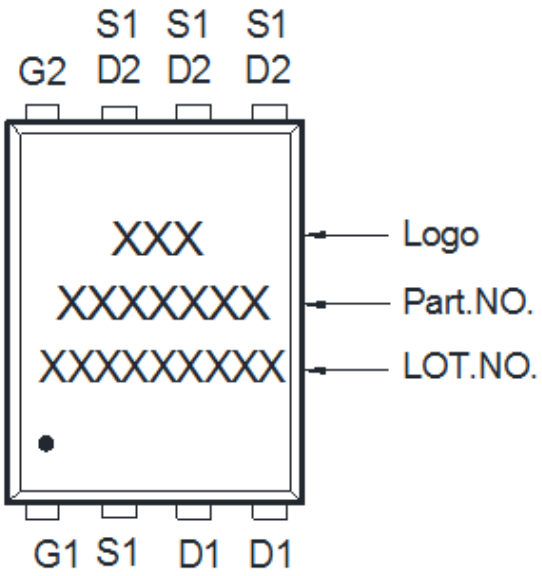
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	1.00		1.20	E3	0.85		1.15
A1	0.00		0.05	E4	1.23		1.53
b	0.30		0.50	e	1.27 BSC		
b1	0.15		0.35	Θ	10° REF		
c	0.15		0.25	L	0.40		0.60
D1	5.05 BSC			L1	1.50		1.70
D	4.80		5.00	L2	0.72		0.92
D2	4.15		4.45	K	0.47 BSC		
D3	3.02		3.32	K1	0.58 BSC		
E1	6.00 BSC			K2	0.50 BSC		
E	5.65		5.85	F	0.695 REF		
E2	2.30		2.60	F1	1.50REF		



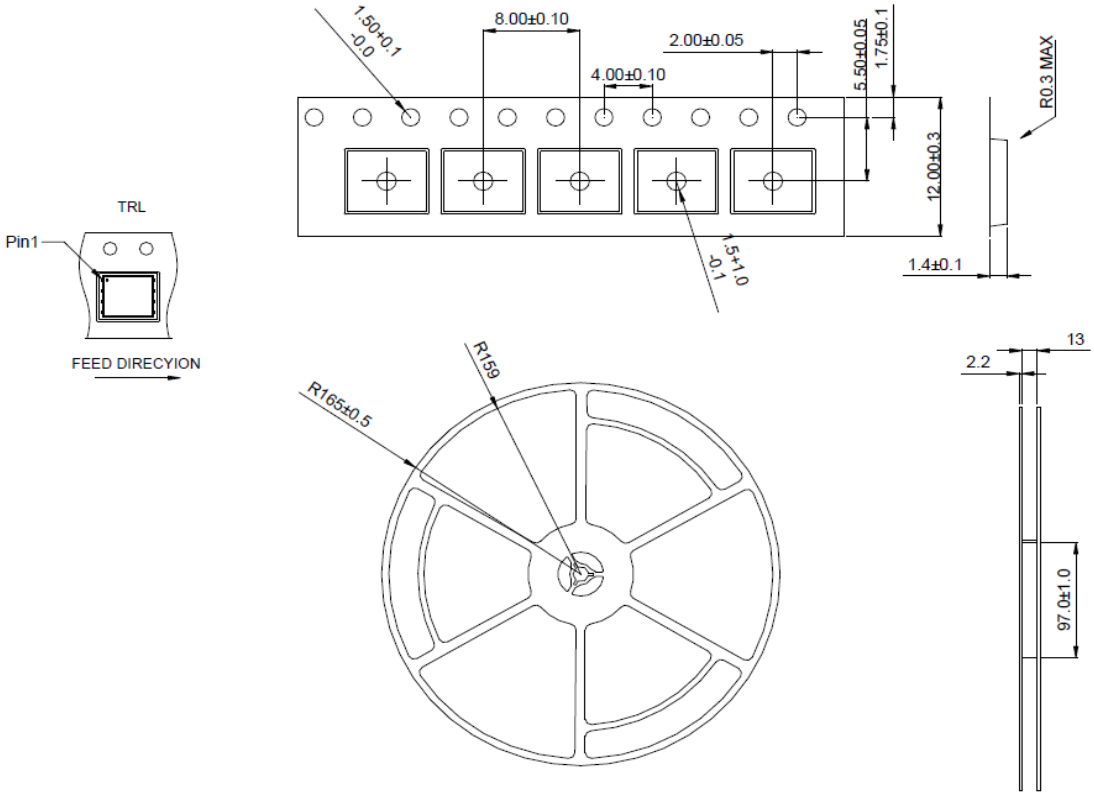
PK610DZ

Dual N-Channel Enhancement Mode MOSFET

A. Marking Information



B. Tape&Reel Information:3000pcs/Reel

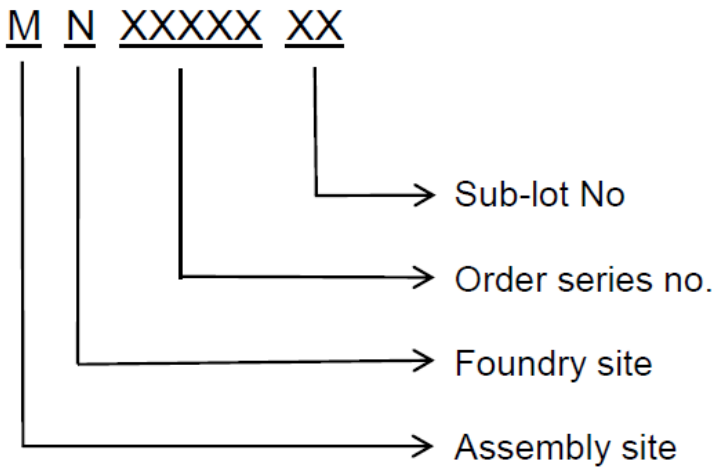


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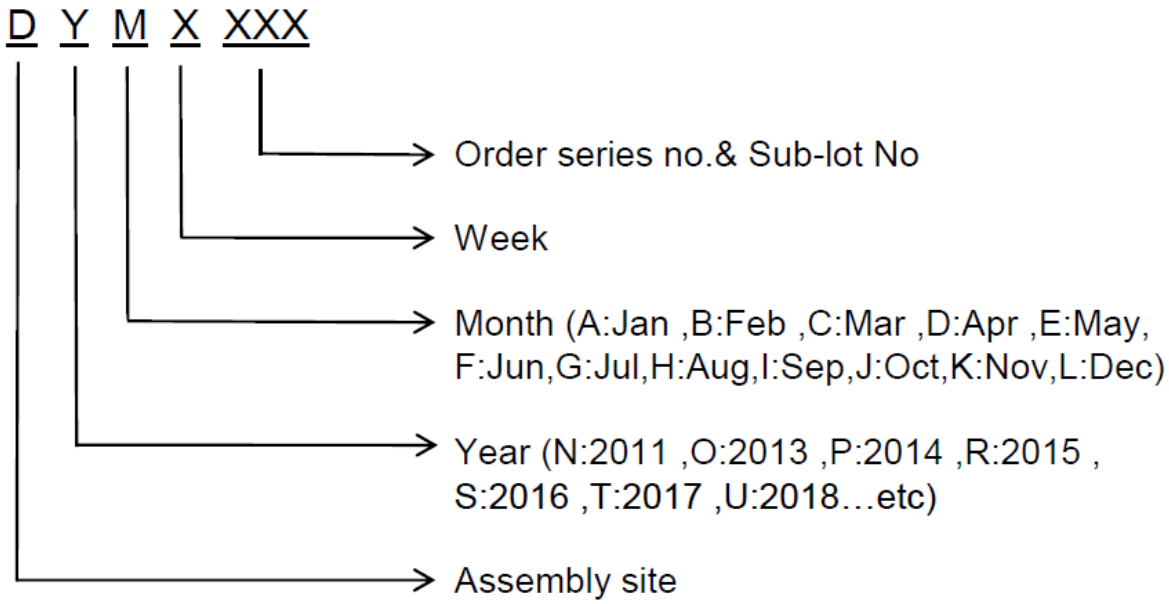
Dual N-Channel Enhancement Mode MOSFET

C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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Dual N-Channel Enhancement Mode MOSFET

D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial （或可区分英文”O”和数字”0”，”G和”Q”的字型即可）
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	RoHS long axis: 12 mm minor axis:6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least